

Progress with EUV optics deposition at RIT

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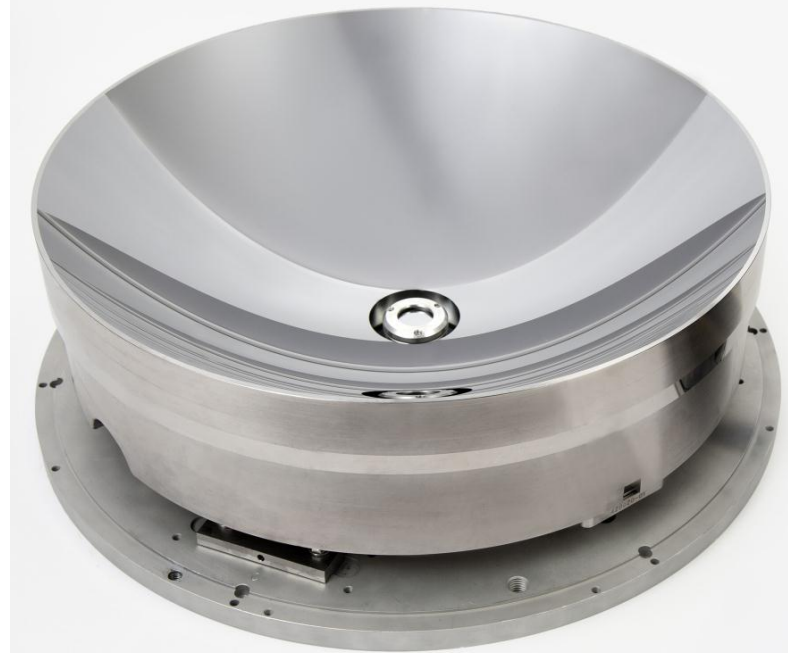
Outline

- Introduction
- New deposition facility
 - ING2 parameters
 - ING2 vs ING1
 - First ML performance
- Clean/Refurb facility
 - New equipment
 - First results
- Conclusion



Collector:

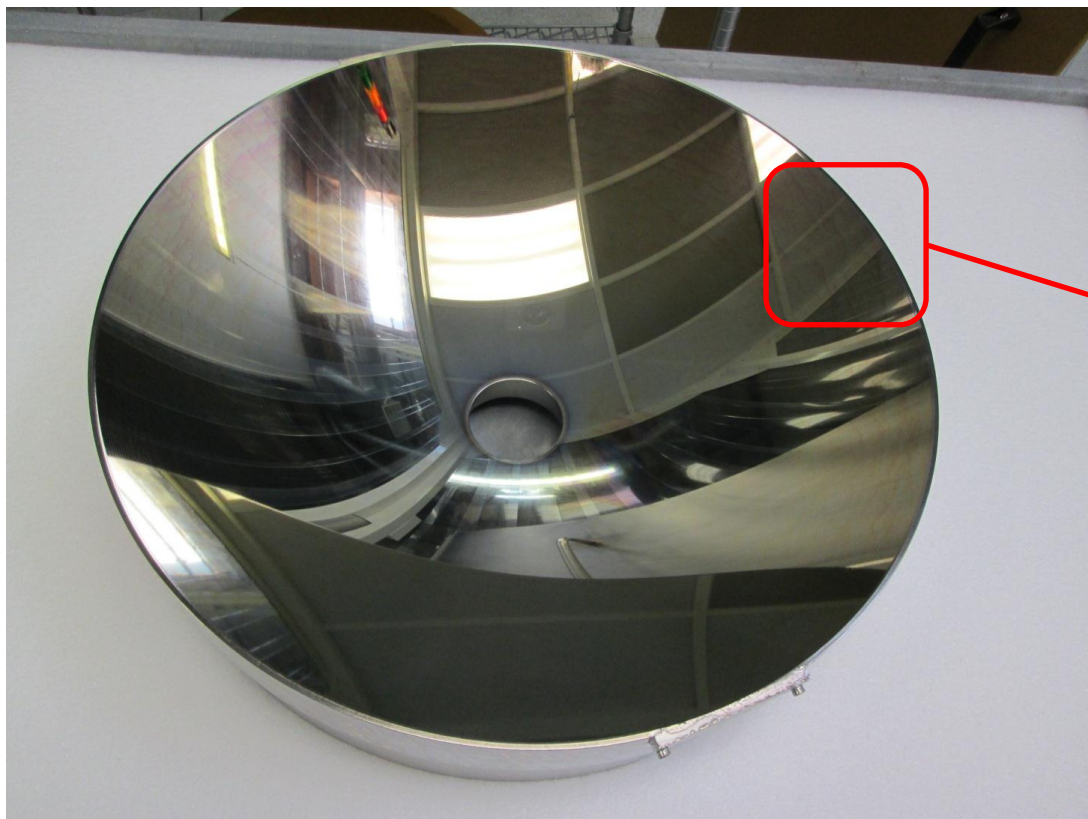
- Demo collector: ~410mm, $NA \gtrsim 0.22$
- IR Suppression (grating): 125X
- Area-weighted EUV Rp: 50.9%
- HVM-ready facility for 750mm optics (Jan-2014)



Refurbishment:

- No Buffer layer: reflectivity loss ~1% - 2% per cycle
- With a buffer layer: reflectivity loss 1.2% after 5 refurbishment cycles
- Removing multilayer top layers by Ion beam etching resulted in a large (6%-12%) loss in EUV reflectivity

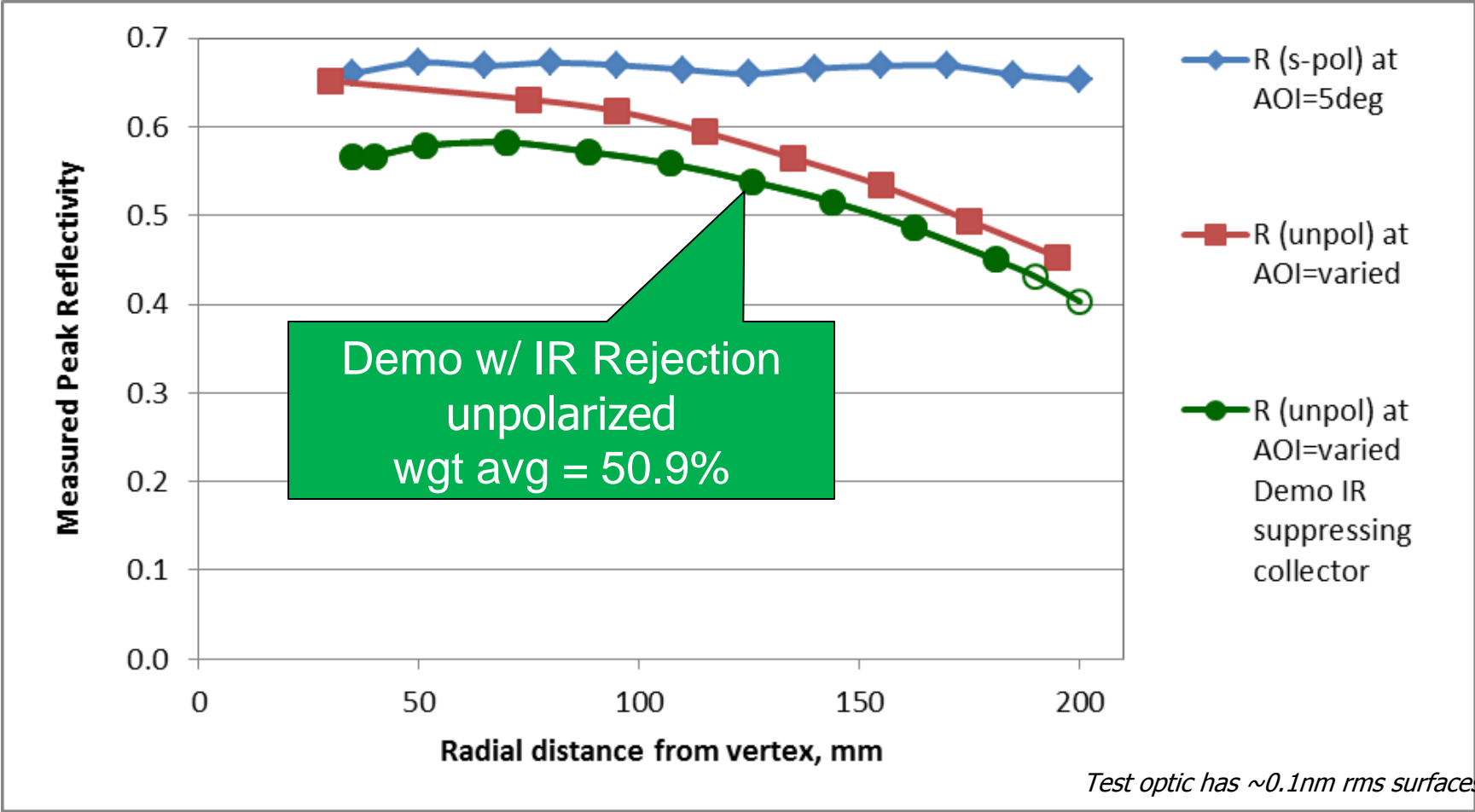
Demonstration Collector: ellipsoidal $\sim 410\text{mm}$ dia ($\text{NA} \gtrsim 0.22$)

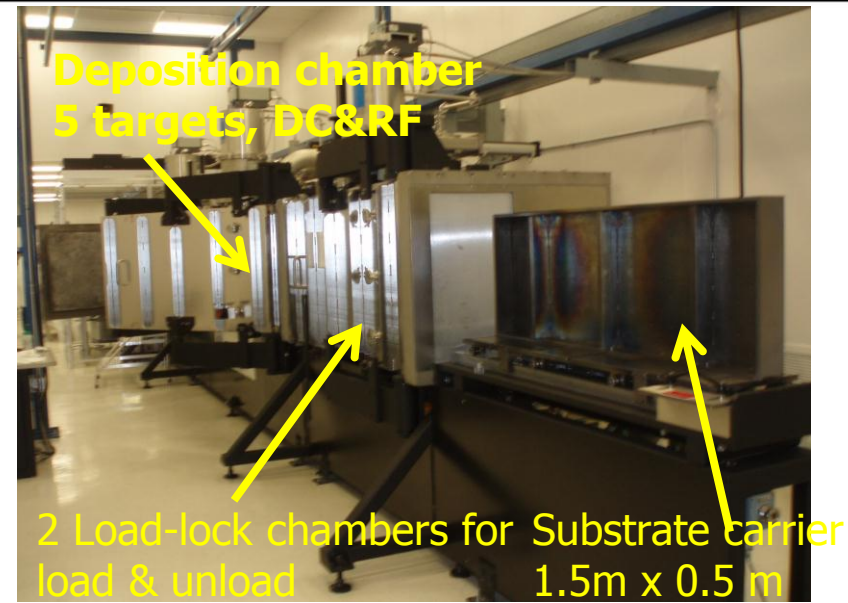
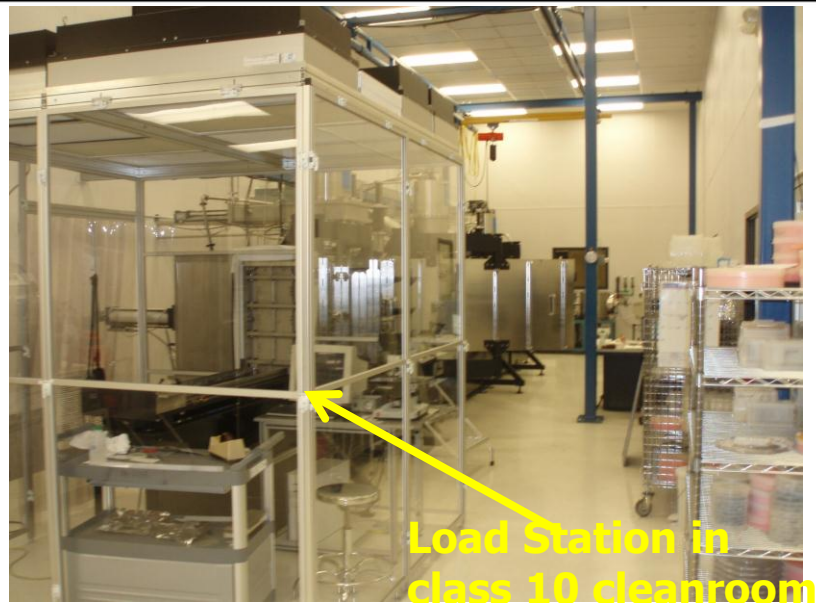


Grating structure

Performance at Design AOI

$\sim 5^\circ$ to $\sim 35^\circ$





Custom built system (1997) – 17 years old

Unique for multilayer production

24/7 operation

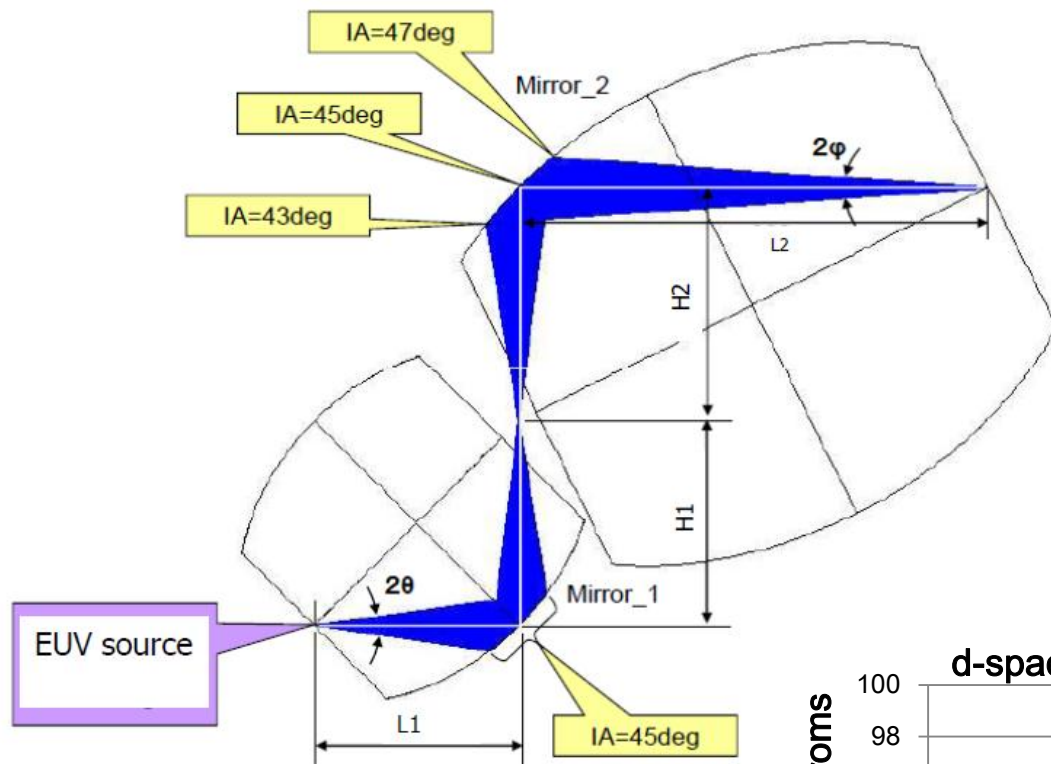
12m long, 2m tall

- Dual Spinning Capability
 - #1: 550mm dia x 220mm thick
 - #2: 175mm dia x 35mm thick
- Mechanical
 - 0.2 mm accuracy
 - 1-100 mm/sec ($\pm 0.1\%$)
 - velocity profiling (6 pts/mm)

Need:

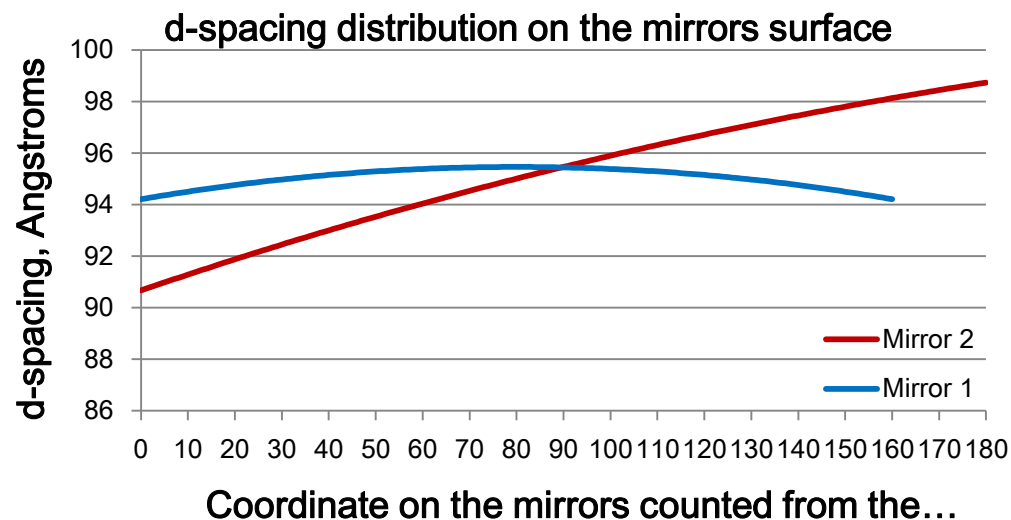
- Larger substrates capability
 - ~ 450 mm ➡ ~ 750 mm
- Better run-to-run repeatability
 - $\pm 0.1\%$ ➡ $< \pm 0.05\%$
- Reactive deposition capability
 - buffer & cap layers
- More flexibility in velocity profiling
-





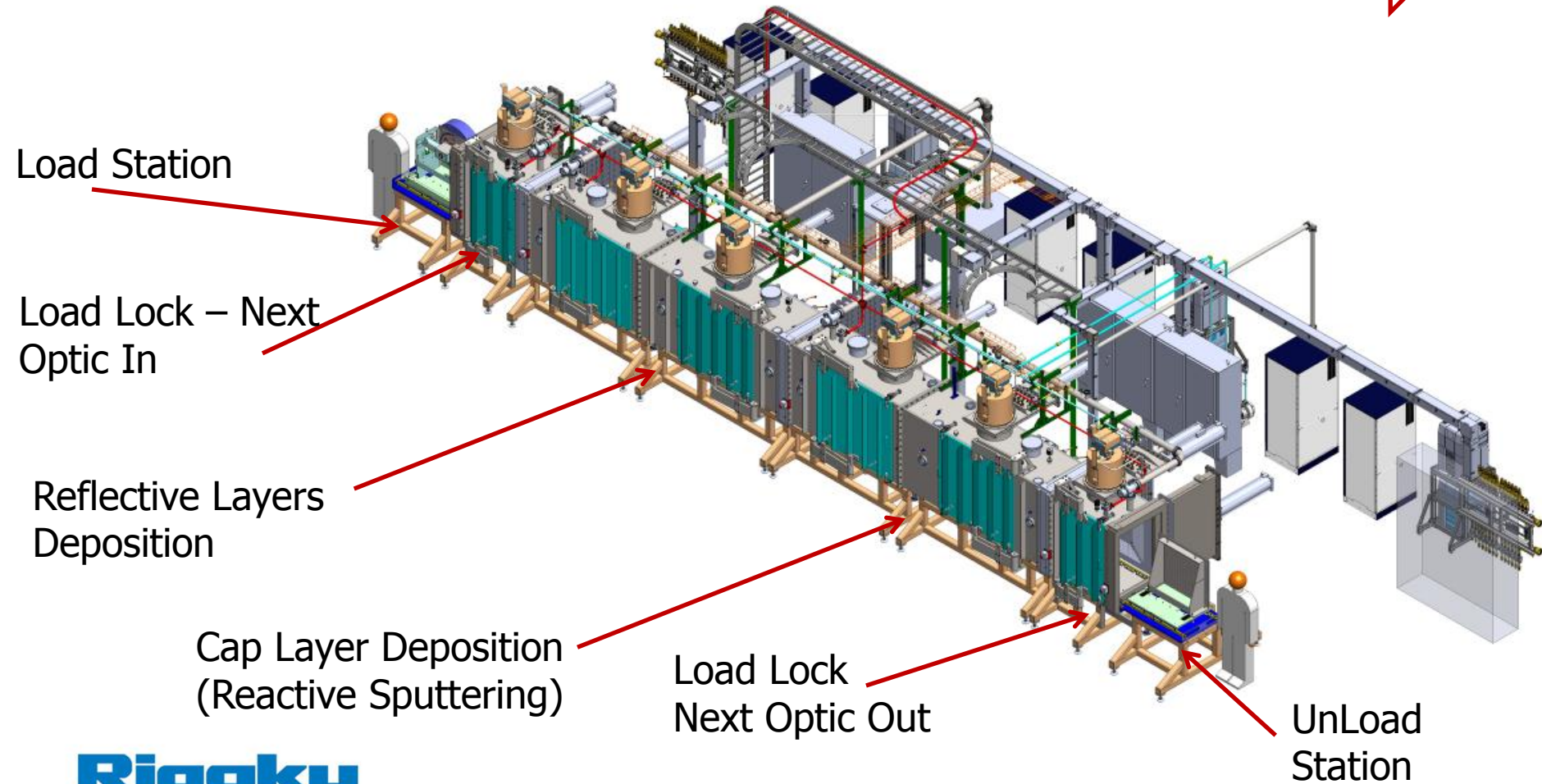
Optical layout

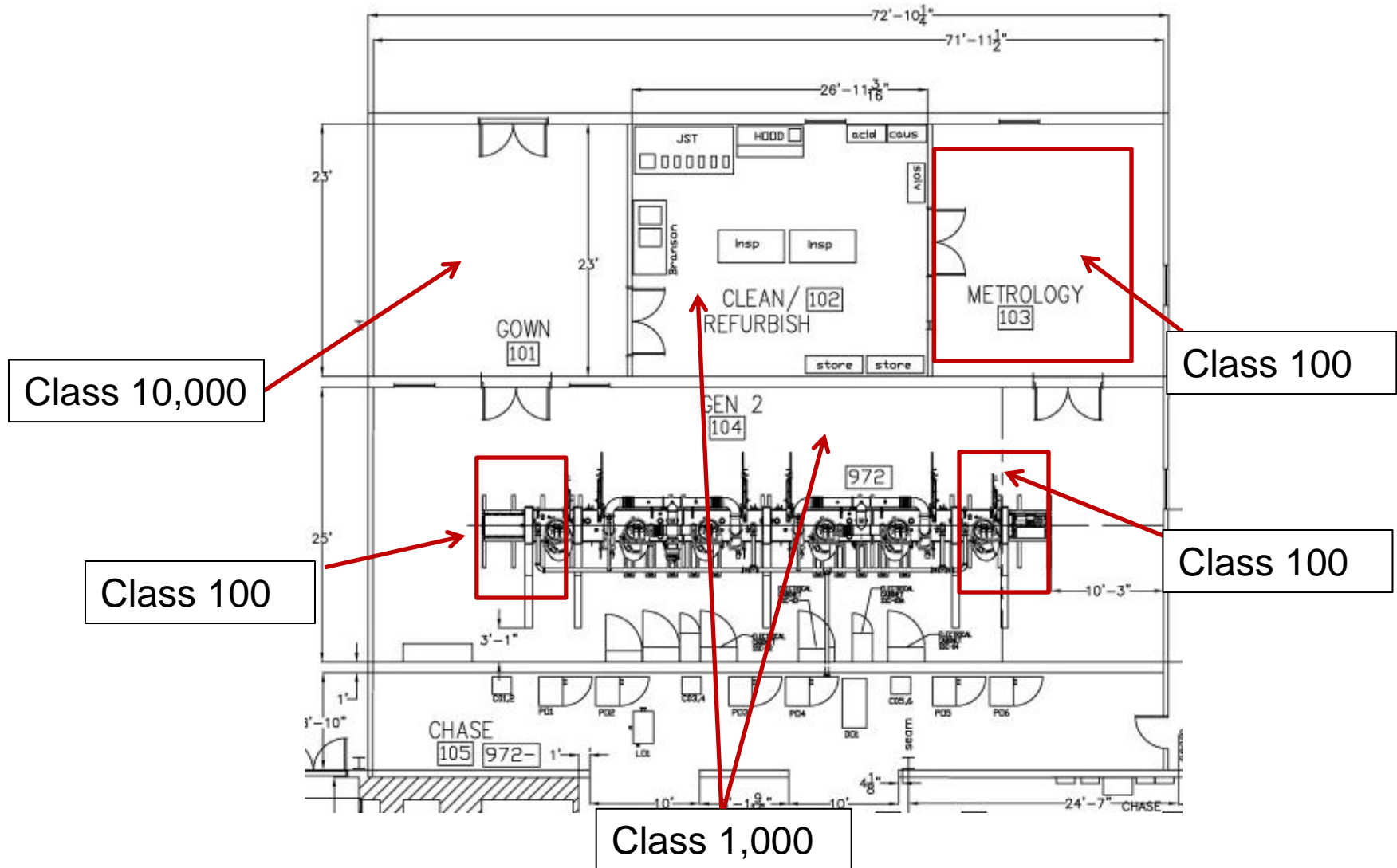
Tangential: graded d-spacing
Sagittal: uniform d-spacing



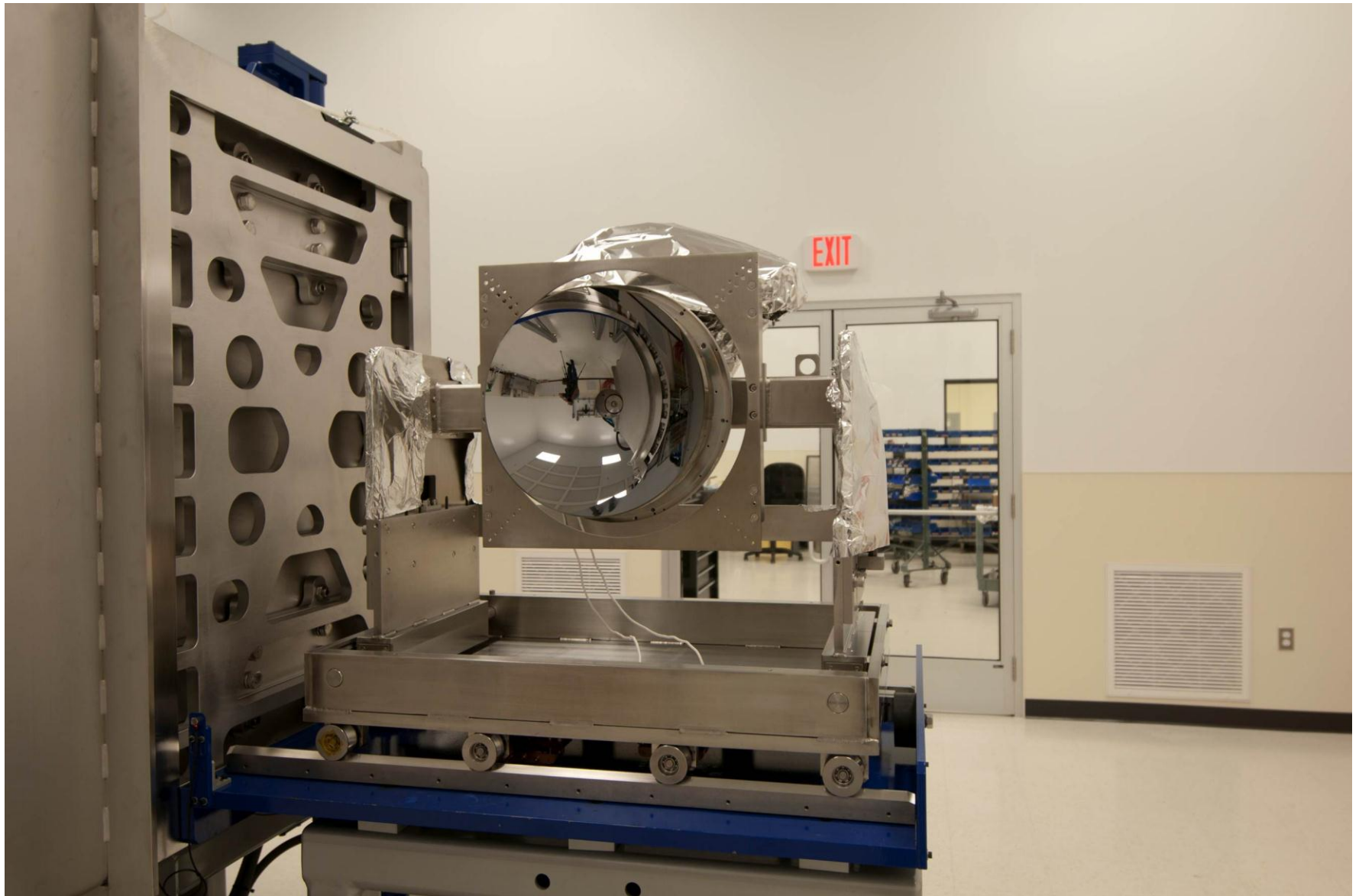
- Up to 750mm DIA optics
- ~UHV, ultra stable
- Expands on 12 years operational learning our Inline1, exclusive to RIT

Production Flow – up to 4 optics simultaneously in process

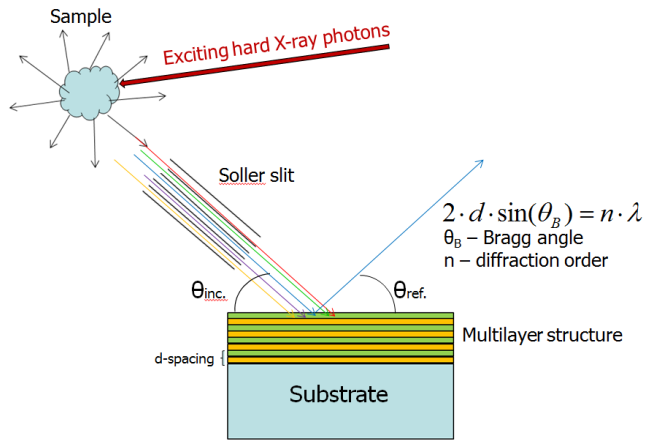












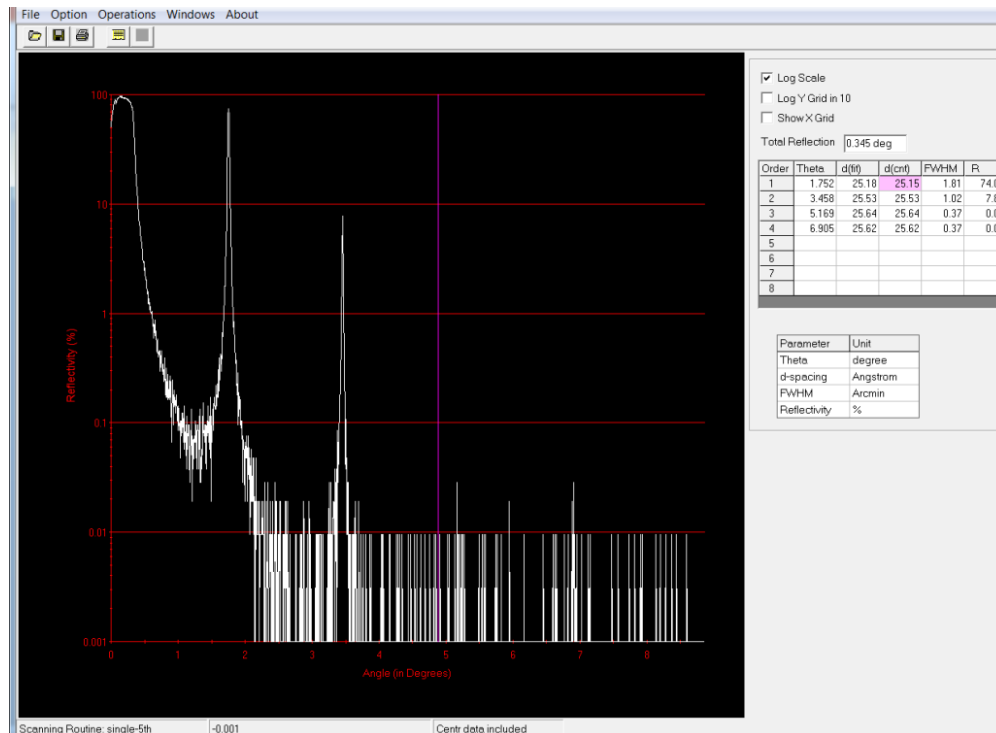
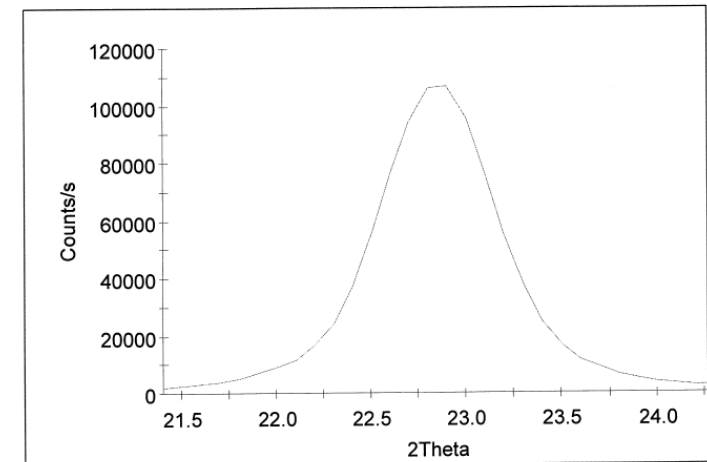
OV050A product W/Si, d=2.5nm, N=175

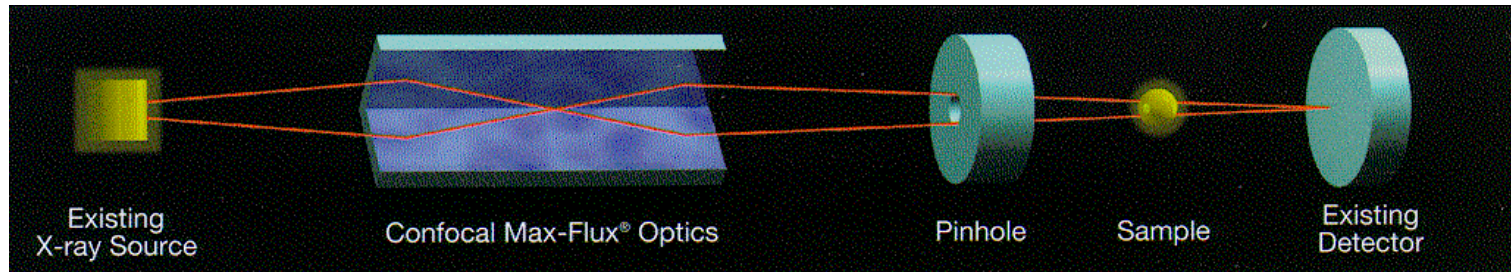
Ovonyx™ Multilayer Product
Vacuum Spectrometer Measurement



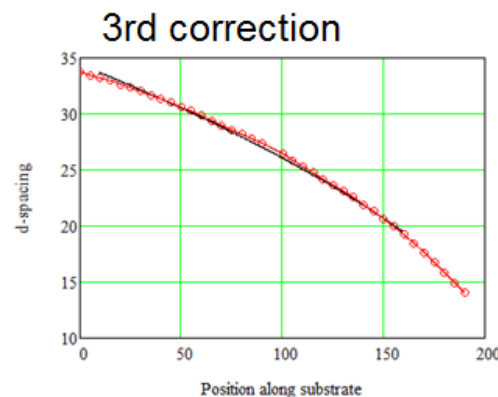
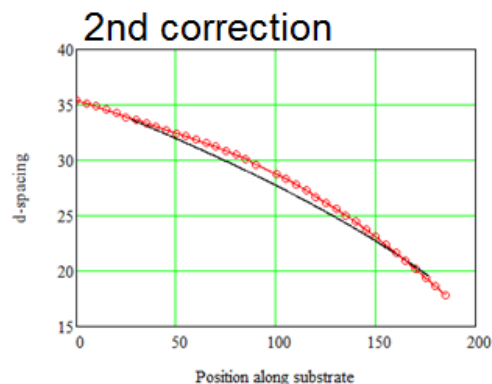
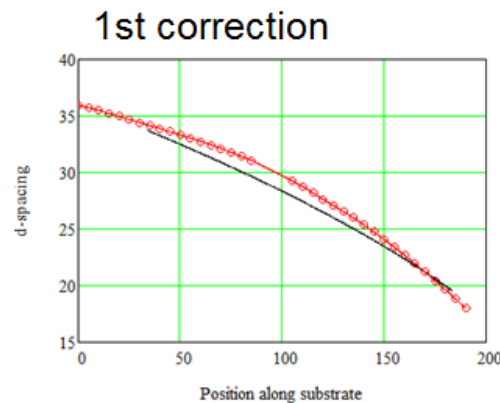
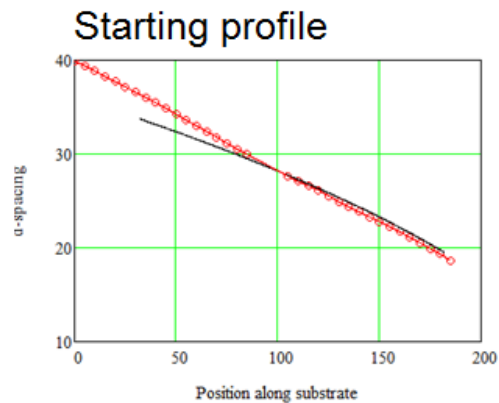
ZSX#	40089
Fluorescer	Mg_Matrix
Wavelength (nm)	0.989
Product	OV050A
Generator KV	31
Generator mA	7

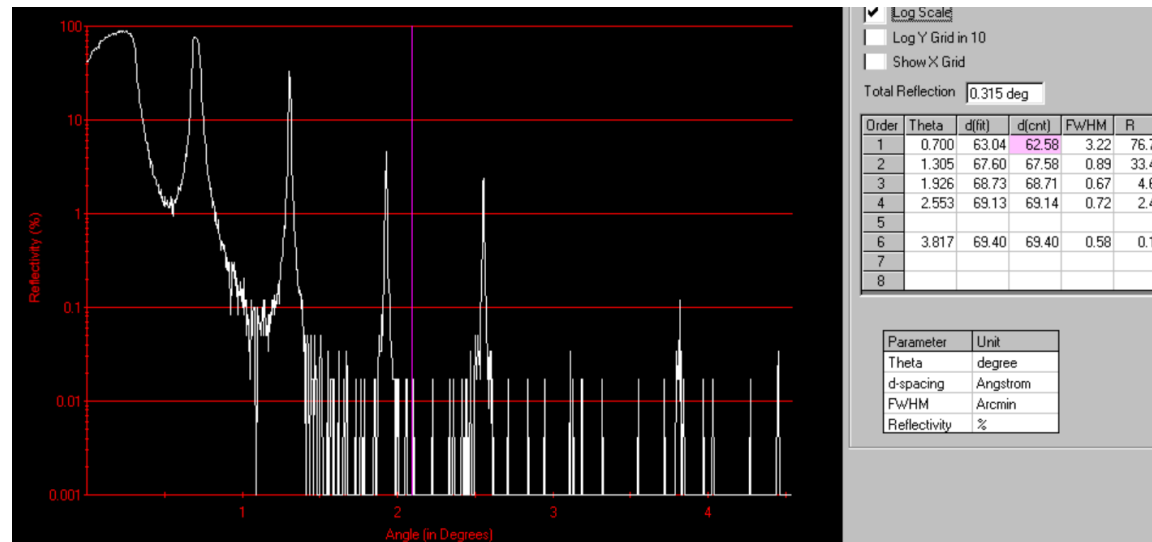
XRO#	38843-4b			
Peak Intensity (cps)	106868.0			
FWHM (2θ)	0.723			
Peak Position (2θ)	22.85			
d-spacing (nm)	2.495			
Δλ/λ (%)	3.12			
Background	λ (nm)	(2θ)	Counts	P/B
Low Angle	n/a			
High Angle	1.104	25.57	698.0	153.10





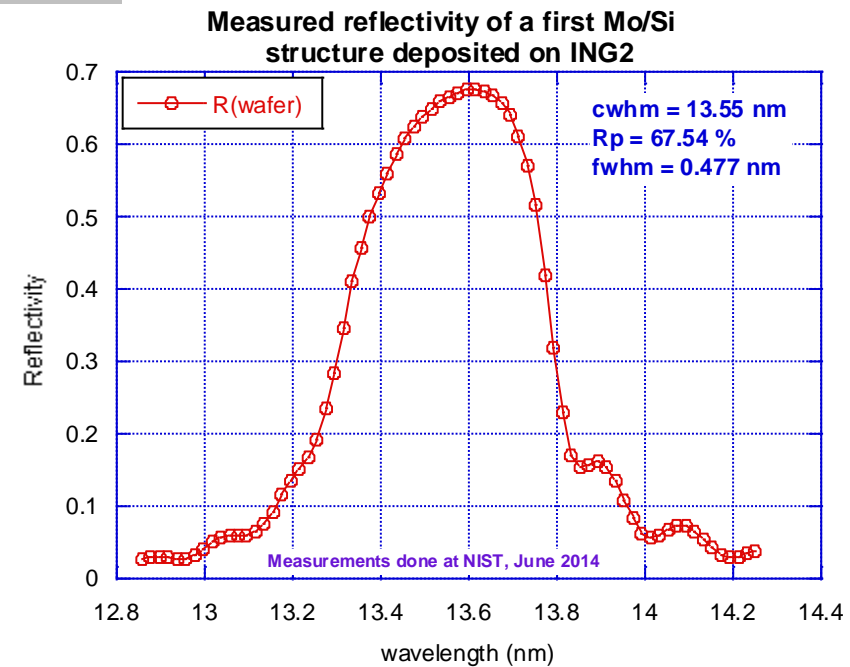
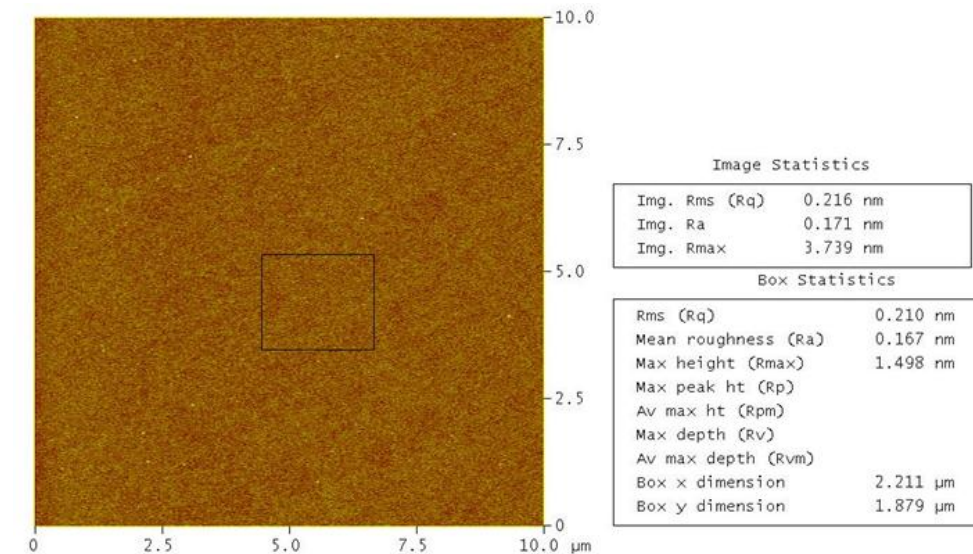
Standard VariMax™ optics
d = 1.9 nm – 3.4nm
150 mm long





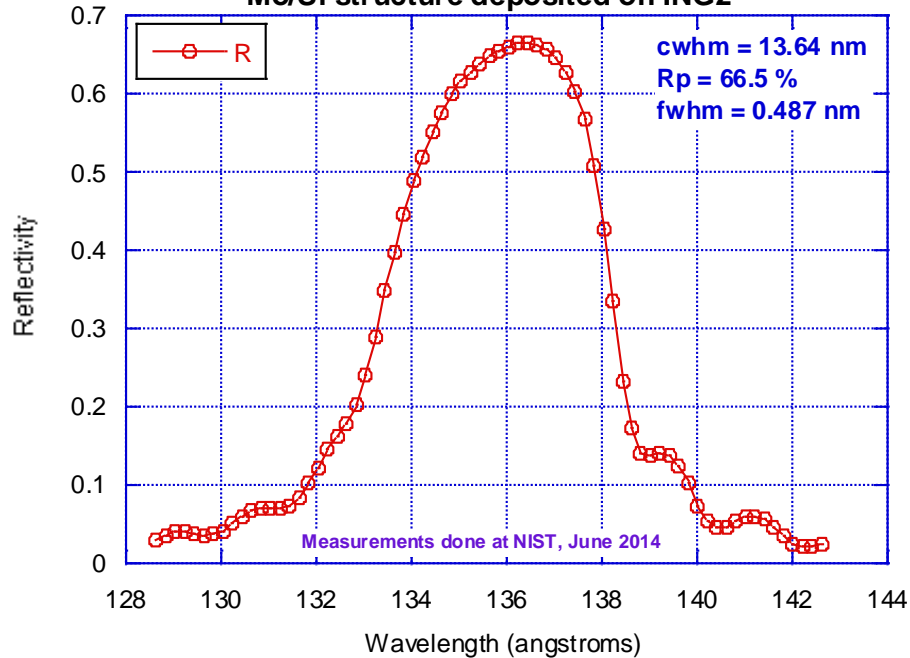
One of the first Mo/Si structures deposited on ING2

No barrier, no cap layers
 $N=60$, $\gamma = 0.4$



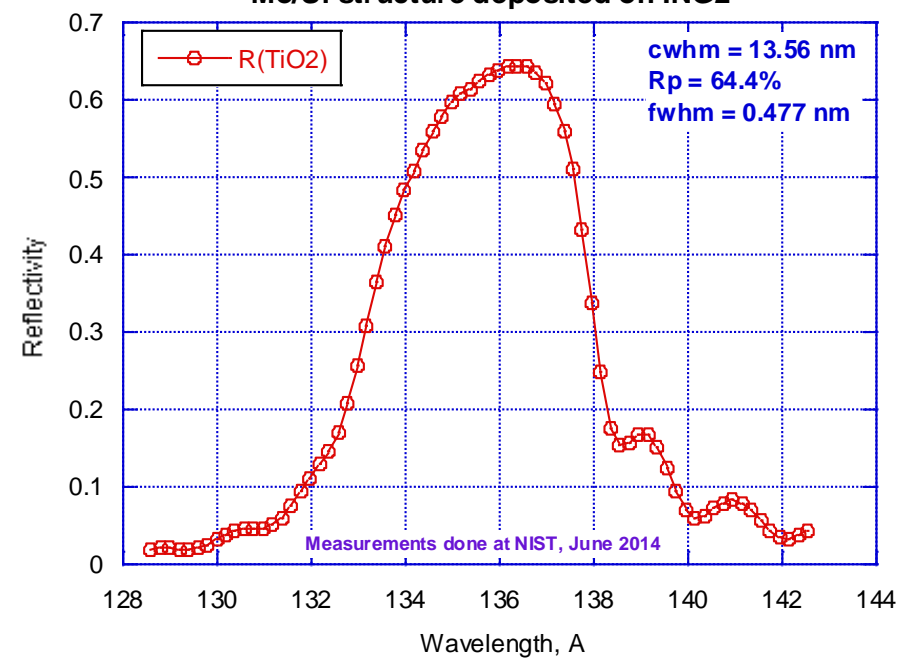
xr039106-s100.002

Measured EUV reflectivity from Ru capped Mo/Si structure deposited on ING2



1% lower than uncapped

Measured EUV reflectivity from TiO2 capped Mo/Si structure deposited on ING2



2% lower than uncapped

Parameters: ING2 vs ING1

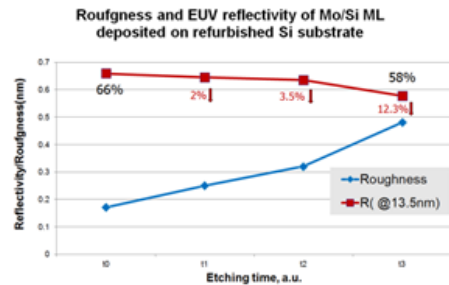
Parameter	Inline G2	Inline G1
Home position	$\leq 0.05\text{mm}$	$\pm 0.2\text{mm}$
Velocity vs. position repeatability	$\leq 0.05\%$	$\sim 5\text{x worse}$
Pump down time	24 hours	48 hours
Base pressure	1×10^{-8} Torr	1×10^{-7} Torr
Target size	30 inches	20 inches
Max. speed of carrier	150 mm/s	100 mm/s
Max. acceleration	150 mm/s^2	10 mm/s^2
Reactive sputtering	yes	limited

Major Advantages

- Much improved vacuum with advanced pumping systems, heaters and polycolds
- Much improved motion control systems for higher accuracy and larger range in position, speed and acceleration
- Fully equipped with multiple gas feeding systems
- Larger targets and full height ion milling capabilities
- Continued operation with load lock systems for high volume production
- Large capacity

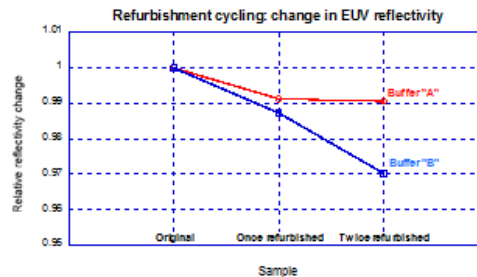
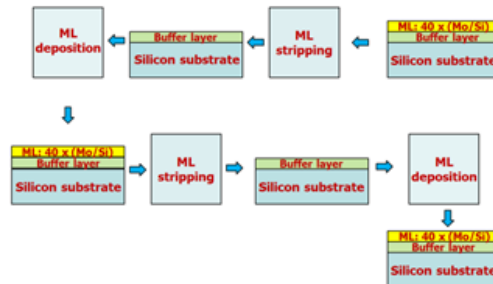
No Buffer layer

Mo/Si multilayer structure with a cap layer deposited on Si substrate – no buffer (current M1-M5 mirrors delivered to EDEC)



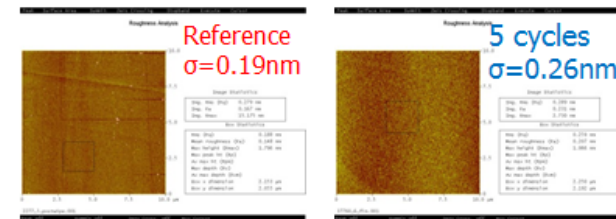
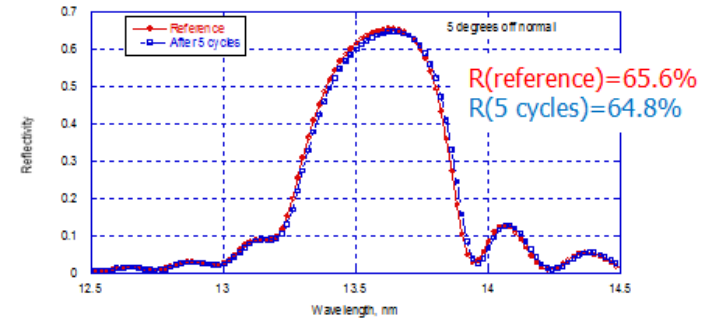
~ 2% loss per cycle with no buffer layer

Introducing a buffer layer (2 cycles - original coating has no buffer layer)



~ 1.9% after 2nd cycle with a buffer layer (no buffer layer in original coating)

5 cycles with a buffer layer (original coating has a buffer layer)



~ 1.2% loss after 5 refurbishment cycles (original coating has a buffer layer)

Etch baths



- Needed
 - Larger size capability
 - Better agitation
 - Better temperature control
 - More baths for multi steps etch-cleaning processes
 - Better safety



Reliable and repeatable results



New Etch/Clean system

- 7 Teflon baths
- Up to 250 mm optics
- Programmable process
- Temperature up to 140°C
- High frequency ultrasonic
- Recirculating pumping



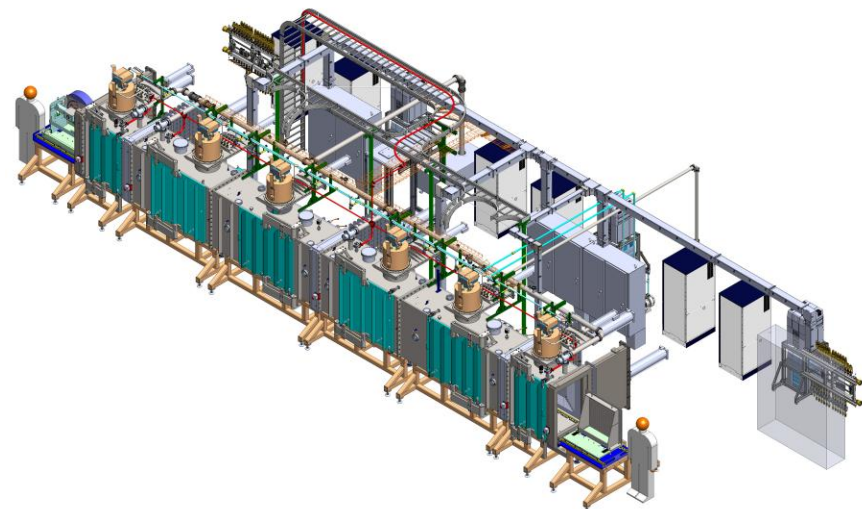
Branson's cleaning system

- 2 stainless steel baths
- Up to 450 mm optics
- Ultrasonic
- Recirculating pumping
- Temperature up to 90°C



New HVM Deposition Facility:

- 750 mm optics deposition capability
- Improved motion control
- Multi gas feeding
- Separate reactive deposition chamber
- High volume production



New Clean / Refurbishment facility:

- Larger sizes (up to 250 mm optics)
- Better agitation with recirculating pumping
- High frequency ultrasonic
- Better temperature control
- Programmable refurb / cleaning process



Jeff Steele and Kermit Jones

from RIT for help with installation the new deposition tool

C. Tarrío, S. Grantham

from NIST and

E. Gullikson

from CXRO

for EUV measurements

Thank you



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